ABSTRACT

METHOD FOR TREATING A SUBSTRATE HAVING A POLYCRYSTALLINE SILICON CARBIDE REAR FACE

The present invention relates to a method for treating a substrate (10) having a back face (204) made of polycrystalline silicon carbide and a front face (203) intended for the manufacture of an electronic component, said method comprising:

the formation of a layer of glassy carbon (40) on the back face (204),

a transfer of a layer (20) of a monocrystalline semiconductor material onto the front face (203),

a heat treatment of the substrate after the formation of the carbon layer (40), said carbon layer (40) limiting the increase in roughness of the back face (204) during the heat treatment.

Figure for the abstract: Fig. 10